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ABSTRACT OF THE DISCLOSURE

A semiconductor device including multiple high-voltage drive transistors in its output section is improved in electrostatic withstand voltage by connecting electrostatic protection transistors in parallel with the high-voltage drive transistors connected to the output pads. The drain withstand voltage of the electrostatic protection transistors is made lower than the drain withstand voltage of the high-voltage drive transistors. In addition, the channel length of electrostatic protection transistors is made short to enable efficient bipolar operation of the electrostatic protection transistors.

Table 1. (continued)	
Case	Reference
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100	100